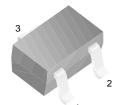


FJX3906

General Purpose Transistor



PNP Epitaxial Silicon Transistor

SOT-323
1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CES}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-200	mA
P _C	Collector Power Dissipation	350	mW
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = -10μA, I _E =0	-40		V
BV _{CEO}	* Collector-Emitter Breakdown Voltage	I _C = -1.0mA, I _B =0	-40		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	-5		V
I _{CEX}	Collector Cut-off Current	V _{CE} = -30V, V _{EB} = -3V		-50	nA
h _{FE}	* DC Current Gain	$\begin{array}{c} V_{CE} = -1 V, I_{C} = -0.1 \text{mA} & 60 \\ V_{CE} = -1 V, I_{C} = -1 \text{mA} & 80 \\ V_{CE} = -1 V, I_{C} = -10 \text{mA} & 100 \\ V_{CE} = -1 V, I_{C} = -50 \text{mA} & 60 \\ V_{CE} = -1 V, I_{C} = -100 \text{mA} & 30 \\ \end{array}$		300	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I_C = -10mA, I_B = -1mA I_C = -50mA, I_B = -5mA		-0.25 -0.4	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C = -10mA, I _B = -1mA -0.65 I _C = -50mA, I _B = -5mA		-0.85 -0.95	V
f _T	Current Gain Bandwidth Product	I _C = -10mA, V _{CE} = -20V 250			MHz
C _{ob}	Output Capacitance	V _{CB} = -5V, I _E =0 f=1.0MHz		4.5	pF
NF	Noise Figure	I_{C} = -10μA, V_{CE} = -5V 4 R_{S} =1KΩ f=10Hz to 15.7KHz		4	dB
t _{ON}	Turn On Time	V _{CC} = -3V, V _{BE} = -0.5V 70 I _C = -10mA, I _{B1} = -1mA		70	ns
t _{OFF}	Turn Off Time	V _{CC} = -3V, I _C = -10mA 300 I _{B1} =I _{B2} =1mA		300	ns

^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Marking S2A

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Typical Characteristics

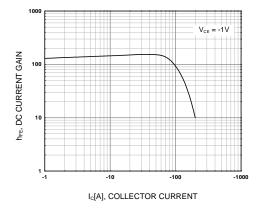


Figure 1. DC current Gain

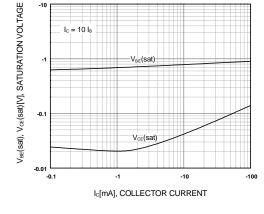


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

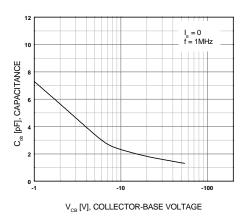


Figure 3. Output Capacitance

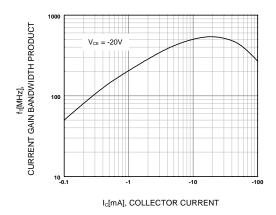
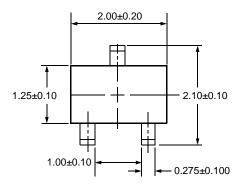
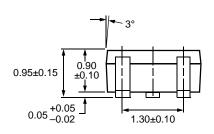


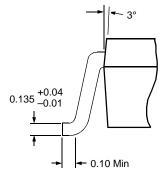
Figure 4. Current Gain Bandwidth Product

Package Dimensions

SOT-323







Dimensions in Millimeters

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